

# NPN-Silizium-Fototransistor Silicon NPN Phototransistor

## SFH 302



### Wesentliche Merkmale

- Speziell geeignet für Anwendungen im Bereich von 450 nm bis 1100 nm
- Hohe Linearität
- TO-18, Bodenplatte, klares Epoxy-Gießharz, mit Basisanschluß
- Gruppierbar

### Anwendungen

- Lichtschranken für Gleich- und Wechsellichtbetrieb
- Industrieelektronik
- „Messen/Steuern/Regeln“

### Features

- Especially suitable for applications from 450 nm to 1100 nm
- High linearity
- TO-18, base plate, transparent epoxy resin lens, with base connection
- Available in groups

### Applications

- Photointerrupters
- Industrial electronics
- For control and drive circuits

Typ Type	Bestellnummer Ordering Code
SFH 302	Q62702-P1641

**Grenzwerte**  
**Maximum Ratings**

Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Betriebs- und Lagertemperatur Operating and storage temperature range	$T_{op}; T_{stg}$	- 40 ... + 80	°C
Löttemperatur bei Tauchlötung Lötstelle $\geq 2$ mm vom Gehäuse, Lötzeit $t \leq 5$ s Dip soldering temperature $\geq 2$ mm distance from case bottom, soldering time $t \leq 5$ s	$T_S$	260	°C
Löttemperatur bei Kolbenlötung Lötstelle $\geq 2$ mm vom Gehäuse, Lötzeit $t \leq 3$ s Iron soldering temperature $\geq 2$ mm distance from case bottom, soldering time $t \leq 3$ s	$T_S$	300	°C
Kollektor-Emitterspannung Collector-emitter voltage	$V_{CE}$	50	V
Kollektorstrom Collector current	$I_C$	50	mA
Kollektorspitzenstrom, $\tau < 10 \mu\text{s}$ Collector surge current	$I_{CS}$	200	mA
Emitter-Basisspannung Emitter-base voltage	$V_{EB}$	7	V
Verlustleistung, $T_A = 25 \text{ °C}$ Total power dissipation	$P_{tot}$	150	mW
Wärmewiderstand Thermal resistance	$R_{thJA}$	450	K/W

**Kennwerte** ( $T_A = 25\text{ °C}$ ,  $\lambda = 950\text{ nm}$ )

**Characteristics**

Bezeichnung Parameter	Symbol Symbol	Wert Value	Einheit Unit
Wellenlänge der max. Fotoempfindlichkeit Wavelength of max. sensitivity	$\lambda_{S\text{ max}}$	880	nm
Spektraler Bereich der Fotoempfindlichkeit $S = 10\%$ von $S_{\text{max}}$ Spectral range of sensitivity $S = 10\%$ of $S_{\text{max}}$	$\lambda$	450 ... 1100	nm
Bestrahlungsempfindliche Fläche Radiant sensitive area	$A$	0.675	mm <sup>2</sup>
Abmessungen der Chipfläche Dimensions of chip area	$L \times B$ $L \times W$	1 × 1	mm × mm
Abstand Chipoberfläche zu Gehäuseoberfläche Distance chip front to case surface	$H$	0.2 ... 0.8	mm
Halbwinkel Half angle	$\varphi$	± 50	Grad deg.
Fotostrom der Kollektor-Basis-Fotodiode Photocurrent of collector-base photodiode $E_e = 0.5\text{ mW/cm}^2$ , $V_{\text{CB}} = 5\text{ V}$ $E_v = 1000\text{ lx}$ , Normlicht/standard light A, $V_{\text{CB}} = 5\text{ V}$	$I_{\text{PCB}}$ $I_{\text{PCB}}$	4.2 12.5	μA μA
Kapazität Capacitance $V_{\text{CE}} = 0\text{ V}$ , $f = 1\text{ MHz}$ , $E = 0$ $V_{\text{CB}} = 0\text{ V}$ , $f = 1\text{ MHz}$ , $E = 0$ $V_{\text{EB}} = 0\text{ V}$ , $f = 1\text{ MHz}$ , $E = 0$	$C_{\text{CE}}$ $C_{\text{CB}}$ $C_{\text{EB}}$	23 39 47	pF pF pF
Dunkelstrom Dark current $V_{\text{CE}} = 10\text{ V}$ , $E = 0$	$I_{\text{CEO}}$	20 ( $\leq 200$ )	nA

Die Fototransistoren werden nach ihrer Fotoempfindlichkeit gruppiert und mit arabischen Ziffern gekennzeichnet.

The phototransistors are grouped according to their spectral sensitivity and distinguished by arabian figures.

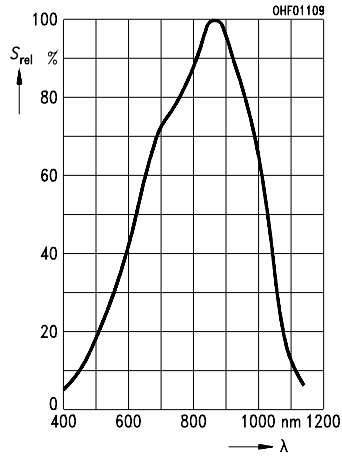
Bezeichnung Parameter	Symbol Symbol	Wert Value					Einheit Unit
		-2	-3	-4	-5	-6	
Fotostrom, $\lambda = 950 \text{ nm}$ Photocurrent $E_e = 0.5 \text{ mW/cm}^2$ , $V_{CE} = 5 \text{ V}$ $E_v = 1000 \text{ lx}$ , Normlicht/standard light A $V_{CE} = 5 \text{ V}$	$I_{PCE}$ $I_{PCE}$	0.4 ... 0.8 1.75	0.63 ... 1.25 2.8	1 ... 2 4.5	1.6 ... 3.2 7.1	$\geq 2.5$ 9.5	mA mA
Anstiegszeit/Abfallzeit Rise and fall time $I_C = 1 \text{ mA}$ , $V_{CC} = 5 \text{ V}$ , $R_L = 1 \text{ k}\Omega$	$t_r$ , $t_f$	9	11	14	17	20	$\mu\text{s}$
Kollektor-Emitter- Sättigungsspannung Collector-emitter saturation voltage $I_C = I_{PCEmin}^{1)} \times 0.3$ , $E_e = 0.5 \text{ mW/cm}^2$	$V_{CEsat}$	200	200	200	200	200	mV
Stromverstärkung Current gain $E_e = 0.5 \text{ mW/cm}^2$ , $V_{CE} = 5 \text{ V}$	$\frac{I_{PCE}}{I_{PCB}}$	140	230	360	570	750	–

<sup>1)</sup>  $I_{PCEmin}$  ist der minimale Fotostrom der jeweiligen Gruppe.

<sup>1)</sup>  $I_{PCEmin}$  is the min. photocurrent of the specified group.

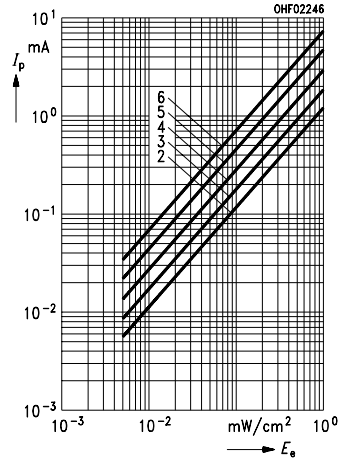
**Relative Spectral Sensitivity**

$S_{rel} = f(\lambda)$



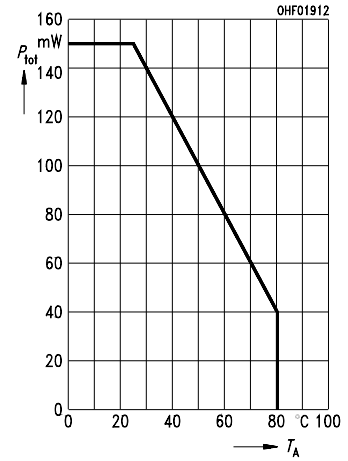
**Photocurrent**

$I_{PCE} = f(E_e), V_{CE} = 5 V$



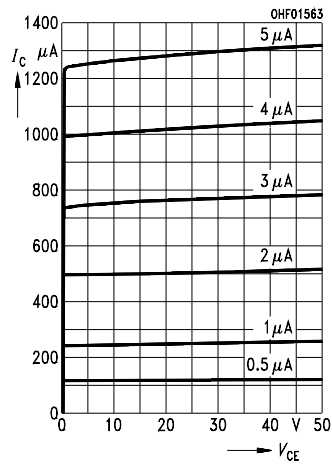
**Total Power Dissipation**

$P_{tot} = f(T_A)$



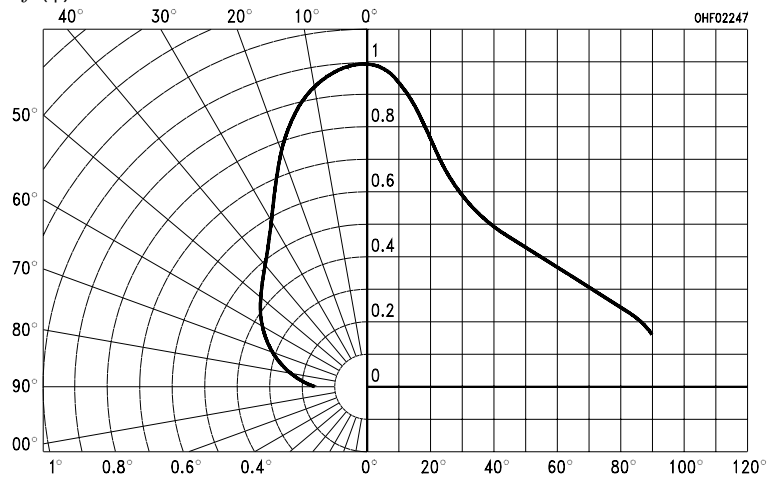
**Output Characteristics**

$I_C = f(V_{CE}), I_B = \text{Parameter}$

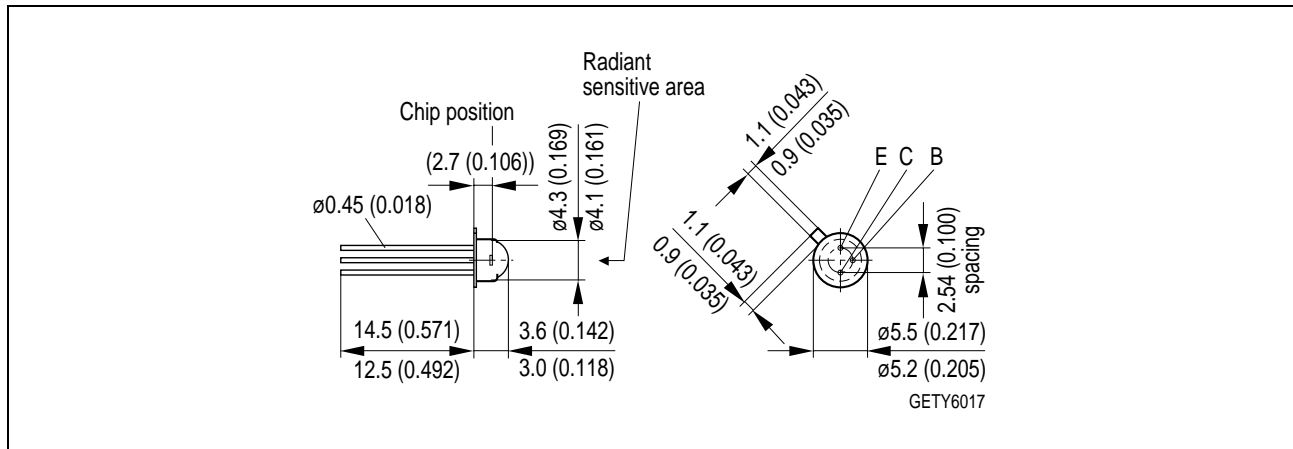


**Directional Characteristics**

$S_{rel} = f(\phi)$



## Maßzeichnung Package Outlines



Maße werden wie folgt angegeben: mm (inch) / Dimensions are specified as follows: mm (inch).

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Please use the recycling operators known to you. We can also help you – get in touch with your nearest sales office. By agreement we will take packing material back, if it is sorted. You must bear the costs of transport. For packing material that is returned to us unsorted or which we are not obliged to accept, we shall have to invoice you for any costs incurred.

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